

SIEMENS

NEW

IL388 HIGH PERFORMANCE LINEAR OPTOCOUPLER for Optical DAA in Telecommunications

Preliminary Data Sheet

FEATURES

- 2.3 mm High SMT Package
- High Sensitivity (K1) at Low Operating LED Current
- Couples AC and DC Signals
- Low Input-Output Capacitance
- Isolation Voltage, 2500 V_{DC}
- Low Distortion, below -80 db
- 0.4 mm Internal Insulation Thickness

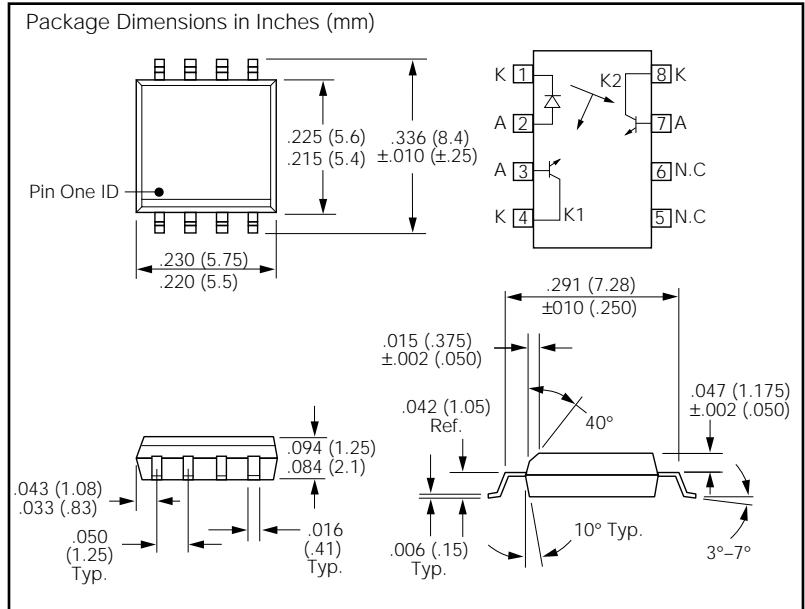
APPLICATIONS

- Optical DAA for V.34 FAX/Modem PCMCIA Cards
- Digital Telephone Line Isolation

DESCRIPTION

The IL388 family of Linear Optocoupler consist of an IRLED optically coupled to two photodiodes. The emitter is located such that both photodiodes receive approximately an equal amount of infrared light. The diodes produce a proportional amount of photocurrents. The ratio of the photocurrents stays constant with high accuracy when either the LED current changes or the ambient temperature changes. Thus one can control the output diode current optically by controlling the input photodiode current.

The IL388 optocouplers can be used with the aid of operational amplifiers in closed loop conditions to achieve highly linear and electrically isolated AC and or DC signal amplifiers.



Absolute Maximum Ratings

Emitter	Sym	Min.	Max.	Units
Reverse Voltage	V _R		3	V
Forward Current	I _F		30	mA
Surge Current Pulse Width < 10 μs	I _{PK}		150	mA
Power Dissipation, T _A =25°C	P _{LED}		150	mW
Derate Linearly from 25°C			2	mW/°C
Junction Temperature	T _J		100	°C
Detector (each)				
Reverse Voltage	V _R		15	V
Power Dissipation	P		50	mW
Derate Linearly from 25°C			0.65	mW/°C
Junction Temperature	T _J		100	°C
Coupler				
Isolation Test Voltage	V _{ISOL}	2500		V _{DC}
Total Package Power Dissipation	P _t		250	mW
Derate Linearly from 25°C			2.8	mW/°C
Storage Temperature	T _S	-40	150	°C
Operating Temperature	T _{OP}	0	75	°C
Lead Soldering Time at 260°C			10	sec.
Isolation Resistance V _{IO} =500 V, T _A =25°C V _{IO} =500 V, T _A =100°C		10 ¹² Ω 10 ¹¹ Ω		

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Electrical Characteristics (T_A=25°C)

LED Emitter	Symbol	Min.	Typ.	Max.	Units	Test Conditions
Forward Voltage	V _F		1.8	2.1	V	I _F =10 mA
Reverse Current	I _R		.01	10	μA	V _R =3 V
V _F Temperature Coefficient	ΔV _F /Δ°C		-2.2		mV/°C	
Junction Capacitance	C _J		TBD		pF	V _F =0 V, f=1 MHz
Dynamic Resistance	ΔV _F /ΔI _F		6		W	
Detector						
Junction Capacitance	C _J		12		pF	V _F =0 V, f=1 MHz
AC Characteristics Photovoltaic Mode						
Frequency Response	BW(-3dB)		1.0		MHz	I _{p1} =25 μA Modulation current ΔI _{p1} =±6 μA
Phase Response			45		Deg.	
Rise Time			350		ns	
Package						
Input-Output Capacitance	C _{IO}		1		pF	V _F =0 V, f=1 MHz
Common Mode Capacitance	C _{cm}		0.5		pF	V _F =0 V, f=1 MHz
Coupled Characteristics			Min.	Typ.	Max.	Units
K ₁ at I _F =2 mA, V _D =0 V			0.007			
THD at f ₀ =316, I _{p1} =35 μA, V _D =0 V			-83			db
K ₃ =K ₂ /K ₁ , I _F =2 mA, V _D =0 V			0.690		1.311	

Bin table for K₃

Bin	Min.	Max.
C	0.690	0.773
D	0.765	0.859
E	0.851	0.955
F	0.945	1.061
G	1.051	1.181
H	1.169	1.311